Paper

# Theoretical Analysis and Improvement of Output Voltage for Resonant Cockcroft–Walton Circuit

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The Cockcroft–Walton (CW) circuit is used in high-voltage low-current apparatuses, such as electron beam irradiation devices and insulation testing devices. The parasitic capacitance of the CW circuit is not considered in the design of a high voltage resonant converter. In the past, it has been clarified that the equivalent capacitor of the CW circuit can be utilized as a resonant capacitor to boost the output voltage. This study derives a theoretical quality factor and an output voltage of a resonant CW circuit, considering the equivalent capacitance and the equivalent conductance. Furthermore, it is revealed that parallel capacitors can improve the quality factor and the output voltage of the CW circuit. Experimental results obtained from the 5-stage resonant CW circuit verify the validity of the theoretical analysis.

Keywords: Cockcroft–Walton circuit, LC resonance, quality factor, boost ratio

#### 1. Introduction

The Cockcroft-Walton (CW) circuit<sup>(1)</sup> has been widely used in many high-voltage/low-current industrial applications where a low-cost and compact system is required such as electron beam irradiation system, insulation testing devices, and so on <sup>(2)-(4)</sup>. The CW circuit has advantages of the simple construction and no active switches. The ideal output voltage of the unloaded N-stage CW circuit is 2N times of the amplitude of the input voltage  $V_{in}$  <sup>(1)</sup>. However, a practical CW circuit has an output voltage drop due to the diode junction capacitors (5)(6). In order to overcome the output voltage drop, several studies have been made such as improved constructions <sup>(5)(7)</sup> and an optimization of parameters <sup>(8)</sup>. The output voltage of the CW circuit becomes close to the ideal output voltage 2NVin thanks to these techniques. However, the output voltage of the CW circuit adopted the previous methods never exceeds the ideal output voltage  $2NV_{in}$  since the previous methods tried to eliminate the influence of the diode junction capacitors.

Generally, isolated high step-up DC-DC converters need to adopt a transformer with large turn ratio. Therefore, parasitic components of the transformer are not ignored for the theoretical analyses. In these converters, a leakage inductor and a winding capacitor in the transformer construct the parallel resonant circuit and boost the output voltage <sup>(3)(9)(10)</sup>. On the other hand, the CW circuit adopted for use in the high step-up DC-DC converters is assumed as a resistor <sup>(11)</sup> or an ideal voltage source <sup>(12)</sup>. Because the equivalent capacitance of the CW circuit is smaller than the winding capacitance of the transformer, it is ignored for the analysis of the converter. Recently, the operating frequency of the converter tends to be higher thanks to the wide-band-gap semiconductors <sup>(13)-(15)</sup>. The high-frequency operation helps to reduce the number of turns and the parasitic components of the transformer. As a result, the equivalent capacitance of the CW circuit cannot be ignored in the high-frequency and high step-up resonant DC-DC converters. Therefore, we revealed that the equivalent capacitor for improvement of the output voltage <sup>(16)</sup>. The previous paper <sup>(16)</sup> theoretically developed the equivalent circuit by approximating only capacitors without resistors.

This paper derives a theoretical output voltage of a resonant CW circuit considering the equivalent capacitor and the equivalent conductor. It is clarified that the additional parallel capacitors improve the output voltage of the resonant CW circuit. Finally, the experimental results reveal the validity of the theoretical analysis. Section 2 describes an operating principle and a theoretical analysis of the resonant CW circuit. Particularly, an output voltage of the proposed resonant CW circuit is derived using a quality factor. An experimental verification is undergone in Section 3. The theoretical output voltage is compared with the experimental one in Section 4.

## 2. Proposed N-stage Resonant CW Circuit

Fig. 1 depicts a proposed *N*-stage resonant CW circuit with parallel capacitors. This section describes a principle and operation states of the proposed *N*-stage resonant CW circuit. Besides, a quality factor and the output voltage are theoretically derived.

**2.1 Principle** The *N*-stage resonant CW circuit involves an inductor *L* in series with the input side and parallel capacitors  $C_r$  in parallel with each diode  $D_1, D_2, \ldots$ , and  $D_{2N}$ . The inductor *L* represents the circuit parasitic inductor,

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Fig. 1. Proposed *N*-stage resonant CW circuit with parallel capacitors



Fig. 2. Equivalent circuit of diode and external parallel capacitor

which is the leakage inductor of the transformer or an additional inductor for the *LC* resonance. As Section 1 mentioned, the conventional CW circuit is generally utilized in the apparatuses that require high-voltage and low-current. Therefore, the ON-period of the diodes is short because of low load current. As a result, the diodes of the conventional CW circuit are regarded as the junction capacitor  $C_t$  in almost period <sup>(5)(17)</sup>.

Fig. 2 shows an equivalent circuit of the diode in the OFFstate <sup>(18)</sup> and the external parallel capacitor. The diode in the OFF-state acts as a resistor  $r_d$  and the junction capacitor  $C_t$ . When the capacitors  $C_1, C_2, \ldots, C_{2N}$  in Fig. 1 is much larger than the sum of the junction capacitor  $C_t$  and the inserted parallel capacitor  $C_r$ , an equivalent circuit of the proposed resonant CW circuit is regarded as only parallel connection of the junction capacitors  $C_t$  and the parallel capacitors  $C_r$ . In other words, the equivalent capacitor  $C_{all}$  of the proposed resonant CW circuit in Fig. 1 is approximately equal to the sum of the junction capacitors  $C_t$  and the parallel capacitors  $C_r$ , whose capacitance is  $2N(C_t + C_r)$ . Therefore, it is considered that the output voltage of the proposed resonant CW circuit can be increased by an *LC* resonance between the inductor *L* and the equivalent capacitor  $C_{all}$ .

Actually, the diode junction resistor <sup>(18)</sup> cannot be ignored for the proposed resonant CW circuit. In the theoretical analysis, the junction resistors in the proposed resonant CW circuit are considered for derivation of the quality factor and the output voltage in this paper.

**2.2 Operation Modes** Fig. 3 illustrates the operation waveforms of the proposed 2-stage resonant CW circuit operating at around the resonant frequency between the inductor L and the equivalent capacitor  $C_{all}$ . Moreover, Fig. 4 draws the operation modes in one period of the proposed 2-stage resonant CW circuit. Here, Label  $i_{Dn}$  ( $1 \le n \le 4$ ) for the current waveform means the current flowing from top to bottom of the diode  $D_n$ . The input voltage  $v_{in}$  is square-wave with amplitude 10 V and the load R is set to 100 k $\Omega$ .

At the first of the positive/negative-half cycle: Mode 1 and



Fig. 3. Voltage and current waveforms of proposed 2stage resonant CW circuit at resonant frequency by numerical simulation



Fig.4. Operation modes of proposed 2-stage resonant CW circuit

Mode 4, all diodes are OFF and they act as the junction capacitors  $C_t$ . The inductor L resonates with the junction capacitors  $C_t$  and the parallel capacitors  $C_r$  in the periods. As a result, the voltage of the power supply and the inductor:  $(v_{in} - v_L)$  is boosted. Accordingly, the output voltage  $V_{out}$ increases. In the modes, the inductor L and the equivalent capacitor  $C_{all}$  act as a parallel resonant circuit <sup>(19)(20)</sup>.

On the other hand, at the second and third of the positive/negative-half cycle: Mode 2-3 and Mode 5-6,  $D_4$ - $D_2$  and  $D_3$ - $D_1$  respectively conduct. The conducting sequences are  $D_4$ - $D_2$  in the positive-half cycle and  $D_3$ - $D_1$  in the negative-half cycle of the input voltage  $v_{in}$  respectively as shown in Mode 2-3 and Mode 5-6. The conduction sequences are also observed in the conventional CW circuit<sup>(3)(21)</sup>. As shown in Fig. 3, the inductor voltage  $v_L$  is constant in Mode 2, 3, 5, and 6. In the mode, the inductor voltage  $v_L$  is clamped to the capacitor voltage. These modes begin after the voltage  $(v_{in} - v_L)$  reaches peak value. Therefore, the voltage at each capacitor is approximately equal to the maximum voltage in Mode 1 and Mode 4.

The operation modes of the proposed *N*-stage resonant CW circuit are almost the same as the proposed 2-stage resonant CW circuit.



Fig. 5. Equivalent circuit of *N*-stage resonant CW circuit considering equivalent circuit of diodes

**2.3 Quality Factor** The proposed resonant CW circuit behaves as a parallel resonant converter composed of the inductor *L*, the junction capacitor  $C_t$ , and the parallel capacitor  $C_r$  as mentioned above. Therefore, a higher quality factor of the converter leads to a higher output voltage<sup>(19)(20)</sup>.

Here, the capacitors  $C_1$ ,  $C_2$ ,..., $C_{2N}$  are assumed to be much larger than the parallel capacitors  $C_r$ . Hence, the equivalent circuit of Fig. 1 is drawn in Fig. 5, which consists of only the inductor *L*, the diodes  $D_1$ ,  $D_2$ ,..., $D_{2N}$ , and the parallel capacitors  $C_r$ . In Fig. 5, the equivalent circuit of the diodes is assumed as the parallel connection of the junction capacitor  $C_t$  and the junction resistor  $r_d^{(18)}$ .

First, the quality factor Q is defined as

where  $\omega$  and  $z(\omega)$  denote an angular frequency of the input voltage  $v_{in}$  and the impedance of Fig. 5, the apostrophe (') is defined as  $d/d\omega$ , and  $\omega_0$  means the resonant angular frequency from  $\text{Im}[z(\omega_0)] = 0^{(22)}$ . Then, the impedance of Fig. 5 is expressed as

$$z(\omega_0) = r_{\rm L} + j\omega_0 L + \frac{1}{G + j\omega_0 C_{\rm all}} \cdots \cdots \cdots \cdots \cdots (2)$$

and

where  $r_{\rm L}$  means the internal resistor of the inductor *L*. In (2), *G* and  $C_{\rm all}$  are defined as  $G = 2N/r_{\rm d}$  and  $C_{\rm all} = 2N(C_{\rm r} + C_{\rm t})$ . Therefore, the quality factor *Q* is derived as

$$Q = \frac{\omega_0}{2} \left| \frac{jL - \frac{jC_{all}}{(G + j\omega_0 C_{all})^2}}{r_L + j\omega_0 L + \frac{1}{G + j\omega_0 C_{all}}} \right| . \dots (4)$$

On the other hand, the resonant angular frequency  $\omega_0$  calculated from  $\text{Im}[z(\omega_0)] = 0$  is obtained as

(4) and (5) lead the quality factor Q as

$$Q = \frac{\omega_0^2 (LC_{\text{all}})^{3/2}}{C_{\text{all}} r_{\text{L}} + LG}$$
 (6)

Next subsection derives the theoretical output voltage using the quality factor Q of the proposed resonant CW circuit. And it is clarified that the higher quality factor Q helps to boost the output voltage. **2.4 Theoretical Output Voltage** As the proposed resonant CW circuit is regarded as a conventional CW circuit whose input voltage is a difference between the input voltage  $v_{in}$  and the inductor voltage  $v_L$ , where  $(v_{in} - v_L)$ , the theoretical output voltage  $V_{out,the}$  can be derived with the conventional calculation method <sup>(5)</sup>.

At first, the voltage  $(v_{in} - v_L)$  from Fig. 5 is expressed as

$$v_{\rm in} - v_{\rm L} = \frac{\frac{1}{G + j\omega_0 C_{\rm all}}}{r_{\rm L} + j\omega_0 L + \frac{1}{G + j\omega_0 C_{\rm all}}} v_{\rm in} \dots (7)$$

As (5) and (6) are assigned to (7), the voltage  $(v_{in} - v_L)$  is given by

$$v_{\rm in} - v_{\rm L} = \frac{Q}{\omega_0^2 (LC_{\rm all})^{3/2} \left(\frac{G}{C_{\rm all}} + j\omega_0\right)} v_{\rm in} \dots \dots \dots (8)$$

The theoretical output voltage of the conventional CW circuit is 2N times as large as the amplitude of the input voltage<sup>(1)</sup>. Hence, an ideal output voltage  $V_{\text{out,idl}}$  of the proposed N-stage resonant CW circuit without the influence of the diode junction capacitors  $C_t$  is obtained in same way as shown in

$$V_{\text{out,idl}} = \frac{2NQ}{\omega_0^2 (LC_{\text{all}})^{3/2} \left\{ \left(\frac{G}{C_{\text{all}}}\right)^2 + \omega_0^2 \right\}^{1/2} V_{\text{in}}, \dots (9)$$

where  $V_{in}$  denotes the amplitude of the input voltage  $v_{in}$ . As (5) is assigned to (9),  $V_{out,idl}$  is deformed as

$$V_{\text{out,idl}} = \frac{2NQ}{\omega_0^2 L C_{\text{all}}} V_{\text{in}} . \qquad (10)$$

It is known that the output voltage drops on account of the diode junction capacitors  $C_t$ <sup>(5)</sup>. In the proposed *N*-stage resonant CW circuit, it is considered that the junction capacitors  $C_t$  and the parallel capacitors  $C_r$  decrease the output voltage. The effect is expressed by voltage efficiency F<sup>(5)</sup>. Therefore, the theoretical output voltage  $V_{\text{out,the}}$  of the *N*-stage resonant CW circuit is derived as

where the voltage efficiency F is expressed as

where *C* denotes capacitance of  $C_1, C_2, \ldots, C_{2N}$ . Here, we explain approximately (11). As the *G* is small enough, (5) is regarded as  $\omega_0^2 \approx 1/LC_{\text{all}}$ , that is,  $\omega_0^2 LC_{\text{all}} \approx 1$ . On the other hand, when  $C_{\text{all}}$  is sufficiently smaller than  $C, F \approx 1$ . From the above, (11) indicates that the output voltage  $V_{\text{out,the}}$  is proportional to the quality factor *Q* only if  $C_{\text{all}}$  is sufficiently smaller than the improvement of the quality factor *Q* contributes to boost the output voltage.

As an example, Fig. 6 shows the ideal relationship between



Fig. 6. Ideal relationship between  $C_r$ , Q, F, and FQ under G = 0.2 mS

 $C_r$ , Q, F, and FQ under  $G = 0.2 \text{ mS}^{\dagger}$ . From (12) and Fig. 6, when  $C_r$  is over 10 pF, the voltage efficiency F starts to decrease. It is not possible to approximate F to 1. Therefore, the output voltage is highly dependent on the FQ. As a result, the optimal  $C_r$  that maximizes the output voltage exists between 100 pF and 1000 pF.

However, it is difficult to consider the junction resistor  $r_d$  and the load *R* separately in the equivalent circuit in Fig. 5 because the CW circuit is treated as a parallel connection of one conductor *G* and one capacitor  $C_{all}$ . Therefore, the equivalent conductor *G* in the Fig. 5 includes the junction resistor  $r_d$  and the load *R* for the following section.

Moreover, the voltage drop occurs due to these resistors. Then, the experimental results of the next section will be lower than the ideal value of this section.

### 3. Experimental Verification

This section experimentally verifies the effectiveness of the proposed resonant CW circuit. The prototype adopts the proposed 5-stage resonant CW circuit. The experimental conditions are listed in Table 1. For comparison about the experimental output voltage  $V_{\text{out,exp}}$ , the parallel capacitor  $C_r$  and the load *R* are changed. Note that the inductor *L* in this paper was made by authors and clear rating cannot be determined.

**3.1 Waveforms** Fig. 7 illustrates the experimental waveforms of the input voltage  $v_{in}$  (CH1), the inductor voltage  $v_L$  (CH3), and the input current  $i_{in}$  (CH2) at the resonant frequency of the proposed resonant CW circuit with  $C_r = 100 \text{ pF}$ . Other conditions are presented in Table 1. The inductor voltage  $v_L$  is boosted and is much larger than the input voltage  $v_{in}$  thanks to the *LC* resonance. It is same characteristics as Fig. 3. On the other hand, the inductor voltage  $v_L$  in Fig. 7 is smaller than the one in Fig. 3 because the simulation results in Fig. 3 has no internal resistor  $r_L$  of the inductor *L*.

Although the input voltage source  $v_{in}$  in Fig. 3 is ideal square wave, the one in Fig. 7 uses a bipolar power supply. Therefore, the input voltage  $v_{in}$  (CH1) has the oscillation when the input voltage  $v_{in}$  changes between positive and negative. At this moment, the inductor voltage  $v_L$  (CH3) shifts several voltages by the input voltage  $v_{in}$  (CH1).

Table I. Experimental co	nditions
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Input voltage	vin	10 V <sub>amp</sub> , square-wave
Inductor	L	$127 \mu\text{H}, 1.2 \Omega$
Capacitors	С	8200 pF, 1600 V
Fast-recovery diodes	$D_1, D_2, \ldots, D_{10}$	(MUR460, 600 V, 4 A)
Parallel capacitor	$C_{\rm r}$	100 pF, 15 kV
		1000 pF, 15 kV



Fig. 7. Experimental input voltage (CH1), inductor voltage (CH3), and input current (CH2) waveforms at resonant frequency with  $C_r = 100 \text{ pF}$ 



Fig. 8. Frequency characteristics of output voltage at each parallel capacitor

**3.2 Frequency Characteristics of Output Voltage Under Various Parallel Capacitors** Fig. 8 depicts the experimental frequency characteristics of thew boost ratio, which is defined as the ratio of the output voltage  $V_{out,exp}$  of the proposed resonant CW circuit to the ideal output voltage 100 V of the conventional CW circuit, under various parallel capacitors  $C_r$ . Other conditions are presented in Table 1. Therefore, a boost ratio greater than 1 means that the output voltage  $V_{out,exp}$  of the proposed 5-stage resonant CW circuit exceeds the ideal and theoretical output voltage of the conventional 5-stage CW circuit. The keys in Fig. 8 show the capacitance of  $C_r$ , and "w/o  $C_r$ " means no parallel capacitor are inserted.

At first, the result at  $C_r = 100 \text{ pF}$  is focused. The maximum boost ratio, which is achieved at the frequency 460 kHz, is about 8.5. The output voltage  $V_{\text{out,exp}}$  exceeds the ideal and the theoretical output voltage of the conventional 5-stage CW circuit. The frequency 460 kHz, where the boost ratio becomes the maximum value, is close to the theoretical resonant frequency 424 kHz calculated from (5). Thus, the output voltage  $V_{\text{out,exp}}$  is considered to be boosted by the *LC* resonance between the inductor *L* and the equivalent capacitor

<sup>&</sup>lt;sup>†</sup> Some parameters;  $C_t$ ,  $C_r$ ,  $C_r$ ,  $r_d$ ,  $r_L$ , and L depend on frequency and voltage. Therefore, these are not uniquely determined. Section 3 estimates the parameters and calculate Q and F.



Fig. 9. Frequency characteristics of output voltage under each load

 $C_{\text{all}}$ .

Secondly, the variations in the boost ratio due to the parallel capacitors  $C_r$  is observed. The maximum boost ratio in the case of no parallel capacitors  $C_r$  also exceeds 1 as shown in Fig. 8. It is considered that the peak boost ratio generated by the *LC* resonance between the inductor *L* and the diode junction capacitors  $C_t$ . On the other hand, although the maximum boost ratio at the parallel capacitor  $C_r = 1000 \text{ pF}$  exceeds 1, it is lower than the maximum boost ratio at  $C_r = 100 \text{ pF}$ . This is caused by the lower quality factor *Q* as detailed in Section 4. In addition, relatively low voltage efficiency *F* also drops the output voltage  $V_{\text{out,exp}}$  in the case of the parallel capacitor  $C_r = 1000 \text{ pF}$ .

**3.3 Frequency Characteristics of Output Voltage Under Various Loads** Fig. 9 depicts the experimental frequency characteristics of the boost ratio under the various loads R at the parallel capacitor  $C_r = 100 \text{ pF}$ . The keys in Fig. 9 show the load resistor of R.

The heavier load *R* leads into the lower output voltage  $V_{\text{out,exp}}$  as shown in Fig. 9. The load current of the proposed resonant CW circuit becomes large on account of the heavier load. Then, the output voltage  $V_{\text{out,exp}}$  decreases and the junction capacitor  $C_t$  and the junction resistor  $r_d$  in the diodes change <sup>(18)</sup>. As a result, the quality factor *Q* in the proposed resonant CW circuit changes and the output voltage  $V_{\text{out,exp}}$  also changes.

## 4. Comparison between Theoretical and Experimental Output Voltage

This section compares the theoretical output voltage  $V_{\text{out,the}}$ in Subsection 2.4 and the experimental output voltage  $V_{\text{out,exp}}$ in Section 3. In order to calculate the theoretical output voltage  $V_{\text{out,the}}$ , the equivalent capacitor  $C_{\text{all}}$  and the equivalent conductor G have to be calculated first. Since the reverse voltage of the diodes in the proposed resonant CW circuit changes from zero to  $2(v_{\text{in}} - v_{\text{L}})$  in the one period, the junction capacitor  $C_{\text{t}}$  and the junction resistor  $r_{\text{d}}$ , which depend on its reverse voltage <sup>(18)</sup>, are changes in the one period. Therefore, the equivalent capacitor  $C_{\text{all}}$  and the equivalent conductor G are obtained with the input impedance, which is calculated from the input voltage  $v_{\text{in}}$  and the input current  $i_{\text{in}}$ , in this paper. The first harmonic approximation is used for the calculation of the equivalent capacitor  $C_{\text{all}}$  and the equivalent conductor  $G^{(23)(24)}$ . As a result, the average value of the

Table	2.	Calculated	l quality	factor	and	output	voltage
under	each	parallel ca	apacitanc	te at $R$	= 1.0	) MΩ	

Parallel capacitance	$C_{\rm r}  [{\rm pF}]$	w/o $C_{\rm r}$	100	1000
Quality factor	Q	6.68	8.46	5.75
Voltage efficiency	F	0.977	0.891	0.534
Theoretical output voltage	Vout, the [V]	719	823	341
Experimental output voltage	Vout,exp [V]	734	845	271
Error	$\varepsilon$ [%]	2.0	2.6	20.5

Table 3. Calculated quality factor and output voltage under each load at  $C_r = 100 \text{ pF}$ 

Load	$R [k\Omega]$	1000	250	111
Quality factor	Q	8.46	7.33	4.10
Voltage efficiency	F	0.891	0.891	0.891
Theoretical output voltage	Vout, the [V]	823	718	416
Experimental output voltage	Vout,exp [V]	845	677	316
Error	$\varepsilon$ [%]	2.6	5.7	24.0

equivalent capacitor  $C_{\text{all}}$  and the equivalent conductor G in the one period are obtained. In addition, the inductor L and internal resistor of the inductor  $r_{\text{L}}$  is measured values. Besides, the diode junction capacitor  $C_{\text{t}}$  in (12) is obtained from the equivalent capacitor  $C_{\text{all}}$  when no parallel capacitors are inserted, where  $C_{\text{t}} = C_{\text{all}}/2N$ .

Table 2 shows the quality factor Q, the voltage efficiency F, the theoretical output voltage  $V_{\text{out,the}}$ , the experimental output voltage  $V_{\text{out,exp}}$ , and the error  $\varepsilon$  under each parallel capacitor at the load resistor  $R = 1.0 \text{ M}\Omega$ . The quality factor Q is the largest at the parallel capacitor  $C_r = 100 \text{ pF}$ , and the output voltage  $V_{\text{out,the}}$  and  $V_{\text{out,exp}}$  also become the largest. Hence, the improvement of the quality factor Q contributes to boost the output voltage  $V_{out,exp}$ . The error  $\varepsilon$ , which is defined as  $\varepsilon = |V_{\text{out,the}} - V_{\text{out,exp}}|/V_{\text{out,exp}}$ , is less than 3% at "w/o  $C_r$ " and " $C_r = 100 \text{ pF}$ " as shown in Table 2. Therefore, (11) is considered to be valid. The error  $\varepsilon$  at "w/o  $C_r$ " and " $C_r = 100 \, \text{pF}$ " is considered to be caused by the measurement error of the inductor L and the resistor  $r_{\rm r}$ . On the other hand, the error  $\varepsilon = 20.7\%$  is relatively large at  $C_r = 1000 \text{ pF}$ . The voltage drop at the capacitors  $C_1, C_2, \ldots, C_{10}$  cannot be ignored since the parallel capacitors  $C_r$  have a value of the capacitor close to the capacitor C at  $C_r = 1000 \text{ pF}$ . As a result, the theoretical output voltage  $V_{\text{out,the}}$  becomes larger than the experimental output voltage  $V_{out,exp}$ .

Table 3 lists the quality factor Q, the voltage efficiency F, the theoretical output voltage  $V_{\text{out,the}}$ , the experimental output voltage  $V_{\text{out,exp}}$ , and error  $\varepsilon$  under each load and parallel capacitance  $C_r = 100 \text{ pF}$ . The heavier load R leads lower theoretical output voltage  $V_{\text{out,exp}}$ . The heavier load R leads lower theoretical output voltage  $V_{\text{out,exp}}$ . The error  $\varepsilon$  becomes larger as the load R becomes heavier because (11) does not consider voltage drop due to the load current.

## 5. Conclusion

This paper derives the theoretical quality factor and the output voltage of the proposed resonant CW circuit considering the equivalent capacitor and the equivalent resistor. It is clarified that the additional parallel capacitors improve the quality factor and the output voltage of the proposed resonant CW circuit. Finally, the experimental results reveal the validity of the theoretical analysis.

This paper does not clarify a specific design procedure of

the inductor and the parallel capacitors because of nonlinear characteristics of the equivalent capacitor and the equivalent conductor in the CW circuit. In future work, a specific design procedure of the inductor and the parallel capacitors will be considered in this research.

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